## 99-0249

The invention refers to the radio electronic engineering and may be used for obtaining thin-filmed heterostructures of the AIIBVI binary compounds for photoresistors and phototransformers manufacturing.

A process for obtaining thin-filmed heterostructures on the A<sup>II</sup>B<sup>VI</sup> binary compounds basis includes vacuum deposition on the support at presence of the temperature gradient between the evaporator and the support, of a compounds stratum with a narrow-band component by means of evaporation in the quasi-closed volume at further heat and chemical treatment and of a compounds stratum with wide-band component by means of discrete evaporation.